

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant	Gregory G. Romas, Jr.	Docket No.:	TI-33156.1
Serial No	TBD	Art Unit:	2813
Filed:	Herewith	Examiner:	Schillinger,Laura
For:	Low Current Blow Trim Fuse	Confirm. No.:	TBD

PRELIMINARY AMENDMENT

Mail Stop Patent Application
 Commissioner of Patents
 P. O. Box 1450
 Alexandria, VA 22313-1450

"EXPRESS MAIL" mailing label number EV 333320181
US. I hereby certify that the Preliminary Amendment and the accompanying Application is being deposited with the United States Postal Service "Express Mail Post Office to Addressee" service under 37 § CFR 1.10 on the above-mentioned date and is addressed to the Mail Stop Patent Application, Commissioner of Patents, P. O. Box 1450, Alexandria, VA 22313-1450.



Allen B. Kroger



SP/4/10
DATE

Sir:

Before examination of the above-identified patent application, please make the following amendments:

IN THE CLAIMS:

Please cancel Claims 1-7 and 10-15 and add new Claims 16-23 which are enclosed on separate pages herewith.

Respectfully submitted,



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Claims:

1-7 (cancelled)

8. (original) A method of forming a trim fuse comprising the steps of:
forming a stepped oxide region on a semiconductor substrate;
forming at least one thinned oxide region on said semiconductor substrate and proximal said stepped oxide region; and
depositing an electrically blowable fuse material on said stepped oxide region and said at least one thinned oxide region to form at least one transition region such that said fuse material changes in thickness as it transitions between said at least one thinned oxide region and said stepped oxide region.

9. (original) The method according to claim 8 wherein said step of depositing an electrically blowable fuse material on said stepped oxide region and said at least one thinned oxide region comprises forming said at least one transition region such that said fuse material reduces in thickness as it transitions from said at least one thinned oxide region to said stepped oxide region.

10-15 (canceled)

16. (new) The trim fuse according to Claim 8 wherein said fuse material comprises metal.

17. (new) The trim fuse according to Claim 9 wherein said fuse material comprises metal.

18. (new) The trim fuse according to Claim 16 wherein said metal comprises Al/Cu.
19. (new) The trim fuse according to Claim 17 wherein said metal comprises Al/Cu.
20. (new) The trim fuse according to Claim 8 wherein said fuse material comprises polycrystal silicon.
21. (new) The trim fuse according to Claim 9 wherein said fuse material comprises polycrystal silicon.
22. (new) The trim fuse according to Claim 8 wherein said semiconductor substrate comprises silicon.
23. (new) The trim fuse according to Claim 9 wherein said semiconductor substrate comprises silicon.